



4. The IGBT according to claim 1, which comprises a short-circuit strap connecting respective two well zones and said semiconductor substrate to one another on surfaces thereof.

5. A method of manufacturing a well zone for the IGBT according to claim 1, which comprises manufacturing horizontal regions of the well zones by one of implantation and diffusion, and manufacturing vertical regions of the well zones by performing at least two epitaxial steps with a subsequent process selected from the group consisting of implantation and diffusion.

6. A method of manufacturing a well zone for the IGBT according to claim 1, which comprises manufacturing horizontal regions of the well zones by one of implantation and diffusion, and manufacturing vertical regions of the well zones by etching trenches and subsequently filling the trenches with doped polycrystalline silicon and diffusing out.

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